

SiC N-MOSFET 1200V, 15mΩ, 117A

Features

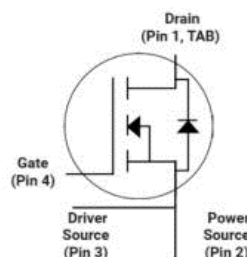
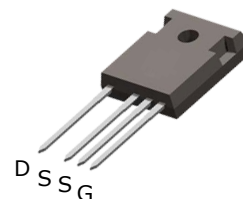
- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Avalanche Ruggednes

Product Summary

V_{DS}	1200V
$R_{DS(on)}_{typ}$	15mΩ
I_D	117A

Applications

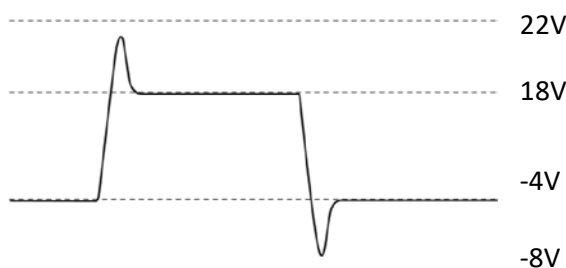
- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC-DC Converters
- Battery Chargers



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	1200	V
Continuous drain current $T_C = 25^\circ\text{C}$, $V_{GS} = 18\text{V}$ $T_C = 100^\circ\text{C}$, $V_{GS} = 18\text{V}$	I_D	117 84	A
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D \text{ pulse}}$	250	A
Gate-Source voltage	V_{GS}	-4/+18	V
Gate-Source voltage (Absolute maximum values)	V_{GSmax}	-8/+22	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	556	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	$^\circ\text{C}$

- Example of acceptable V_{GS} waveform



Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R_{thJC}	0.27	$^{\circ}C/W$
Thermal resistance, junction – ambient. Max	R_{thJA}	40	

Electrical Characteristic (at $T_j = 25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	1200	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	$V_{DS}=V_{GS}, I_D=25mA$
Zero gate voltage drain current	I_{DSS}	-	1	50	μA	$V_{DS}=1200V, V_{GS}=0V$ $T_C=25^{\circ}C$
		-	10	-		$T_C=175^{\circ}C$
Gate-source leakage current	I_{GSS}	-		200	nA	$V_{GS}=18V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	15	22	m Ω	$V_{GS}=18V, I_D=80A,$ $T_J=25^{\circ}C$
		-	29	-		$T_J=175^{\circ}C$
Transconductance	g_{fs}	-	27	-	S	$V_{DS}=20V, I_D=40A$

Dynamic Characteristic

Input Capacitance	C _{iss}	-	4508	-	pF	V _{DS} = 1000V V _{GS} = 0V T _J = 25°C V _{AC} = 25mV f = 1MHz
Output Capacitance	C _{oss}	-	214	-		
Reverse Transfer Capacitance	C _{rss}	-	26	-		
Gate Total Charge	Q _G	-	222	-	nC	V _{DS} = 800V V _{GS} = 0/18V I _D = 80A
Gate-Source charge	Q _{gs}	-	46.4	-		
Gate-Drain charge	Q _{gd}	-	77.6	-		
Turn-On Switching Energy	E _{ON}	-	2.29	-	mJ	V _{DD} = 800V V _{GS} = -4/+18V I _D =80A R _G = 5Ω L = 120uH
Turn-Off Switching Energy	E _{OFF}	-	0.63	-		
Turn-on delay time	t _{d(on)}	-	49.2	-	ns	
Rise time	t _r	-	14.2	-		
Turn-off delay time	t _{d(off)}	-	21.7	-		
Fall time	t _f	-	11.3	-		
Gate resistance	R _G	-	0.9	-	Ω	V _{AC} = 25mV, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}		4.4		V	$V_{GS} = -4V, I_{SD} = 40A,$ $T_J = 25^{\circ}C$
			3.9			$V_{GS} = -4V, I_{SD} = 40A,$ $T_J = 175^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	29.6	-	ns	$V_R = 800V$ $I_D = 80A$ $di/dt = 1000A/\mu S$ $T_J = 25^{\circ}C$
Body Diode Reverse Recovery Charge	Q_{rr}	-	272	-	nC	

Typical Performance Characteristics

Fig 1. Output Characteristic ($T_J = -55^\circ\text{C}$)

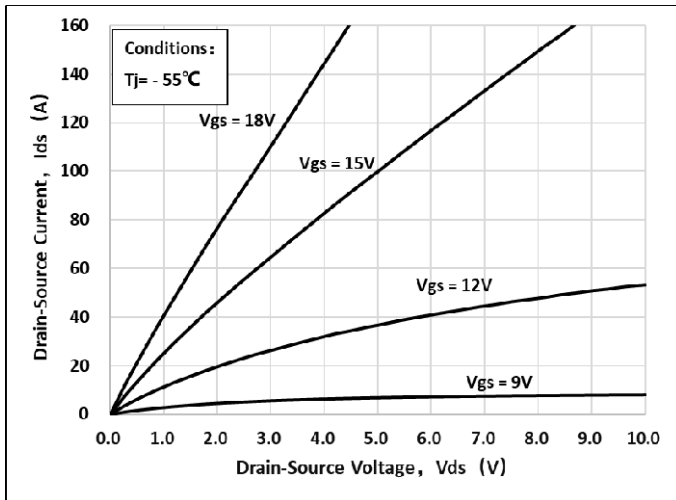


Fig 2. Output Characteristic ($T_J = 25^\circ\text{C}$)

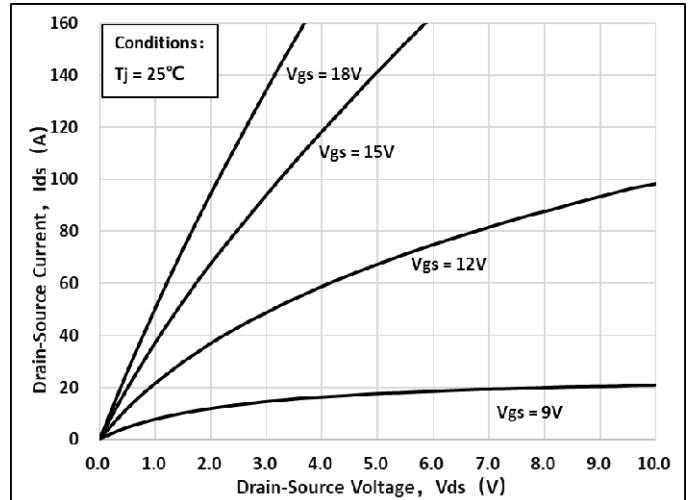


Fig 3. Output Characteristic ($T_J = 175^\circ\text{C}$)

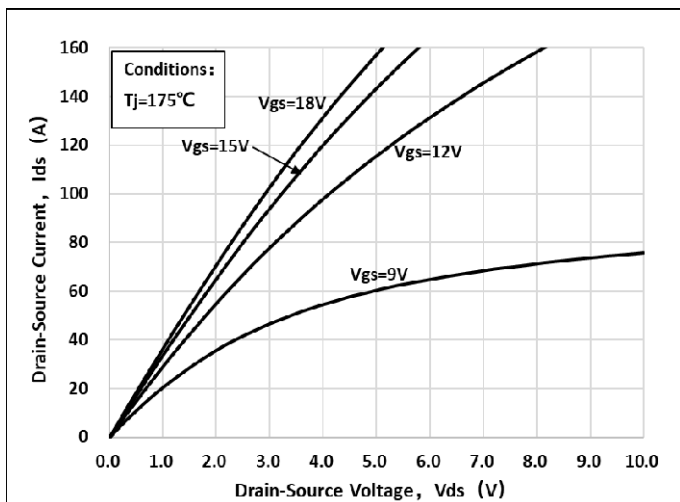


Fig 4: $R_{DS(on)}$ Vs I_{DS} Characteristic

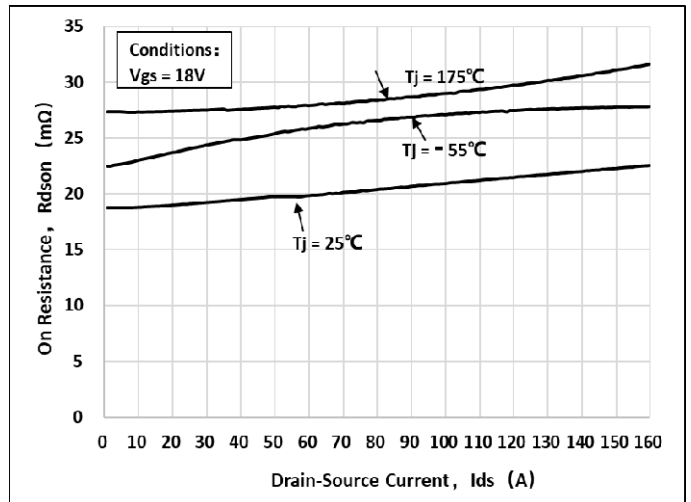


Fig 5: $R_{DS(on)}$ vs. Temperature

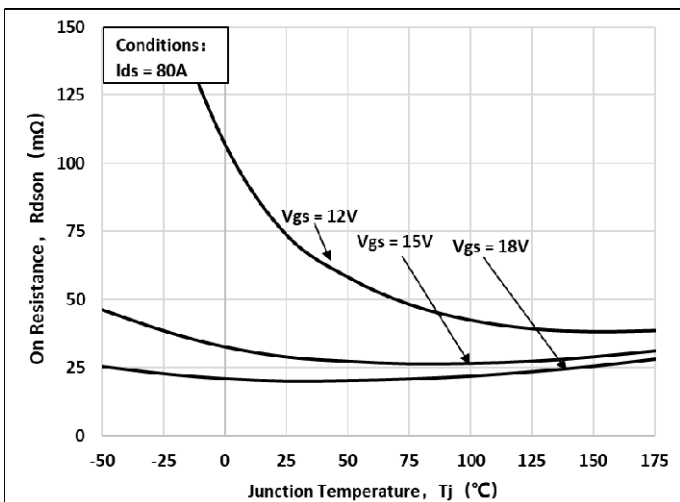


Fig 6: Transfer Characteristic

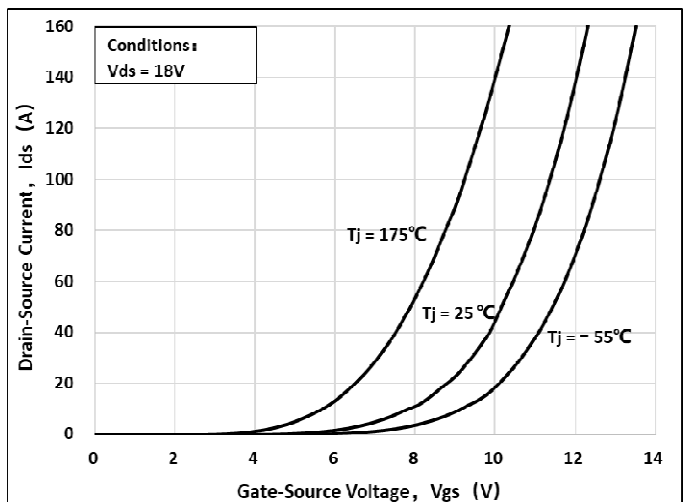


Fig 7: Body-diode Characteristic ($T_J = -55^\circ\text{C}$)

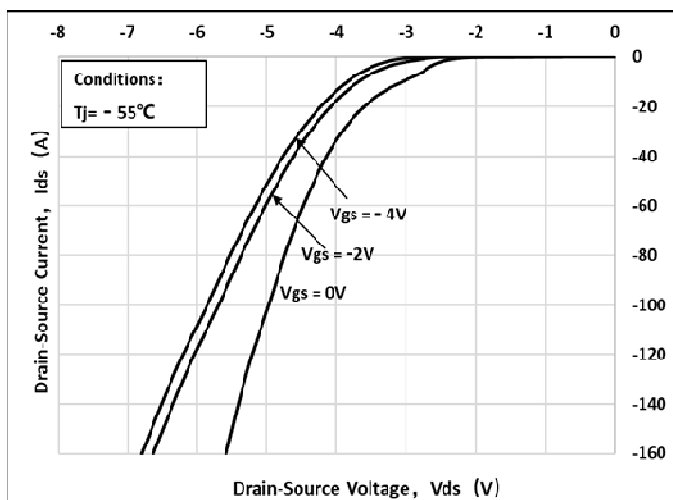


Fig 8: Body-diode Characteristic ($T_J = 25^\circ\text{C}$)

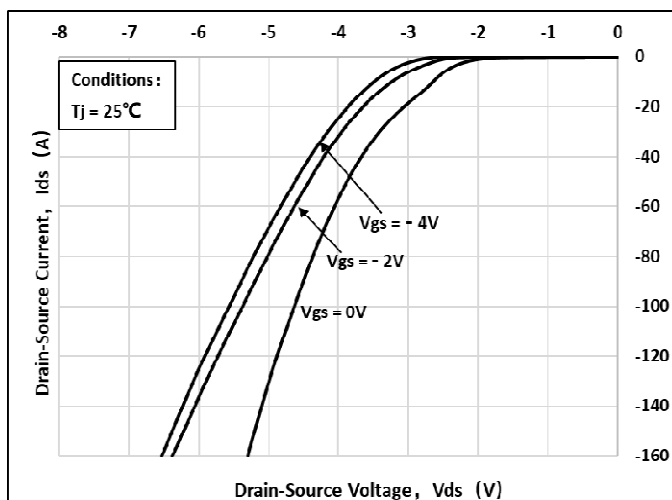


Fig 9: Body-diode Characteristic ($T_J = 175^\circ\text{C}$)

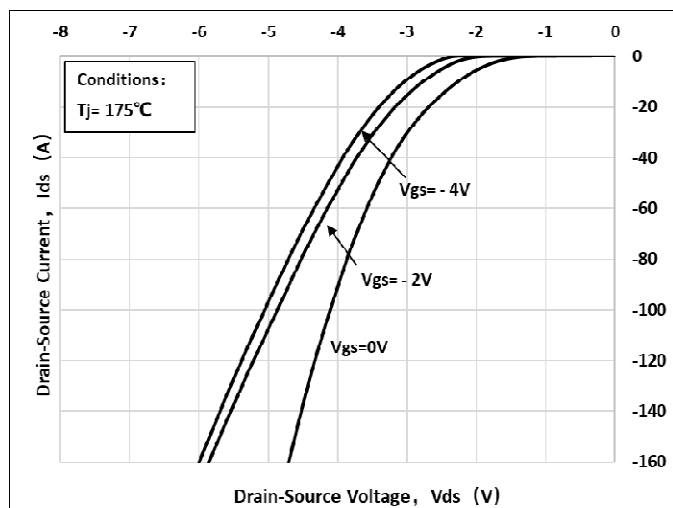


Fig 10: V_{TH} Vs T_J Temperature Characteristic

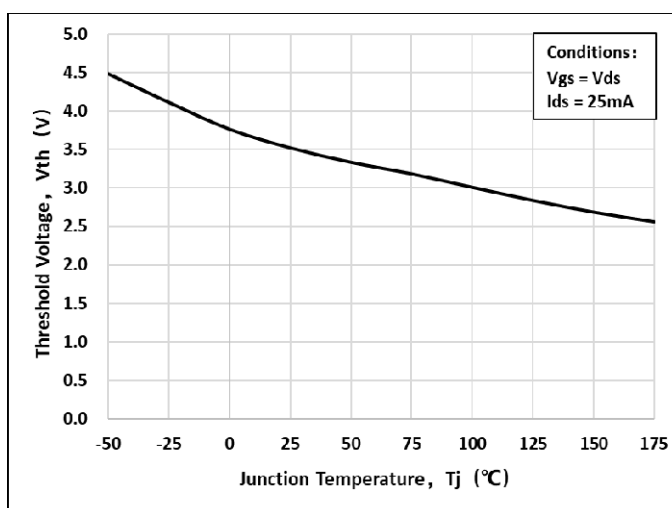


Fig 11: Gate Charge Characteristics

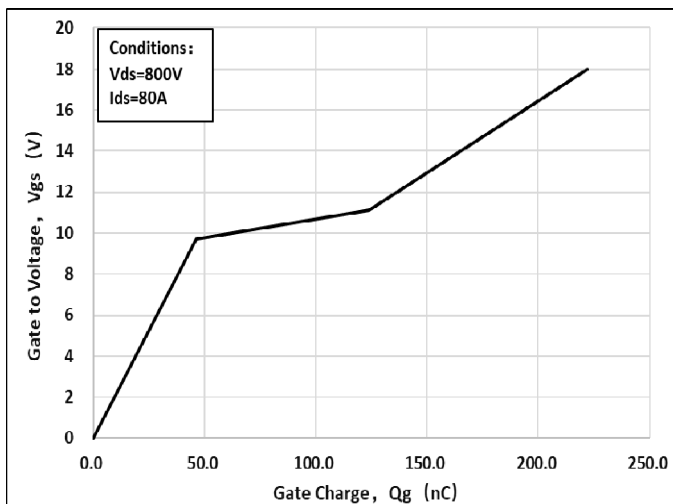


Fig 12: 3rd Quadrant Characteristic ($T_J = -55^\circ\text{C}$)

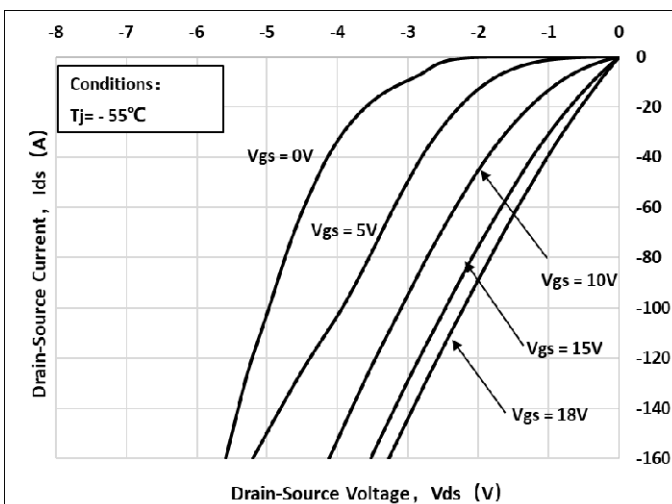


Fig 13: 3rd Quadrant Characteristic($T_J=25^\circ\text{C}$)

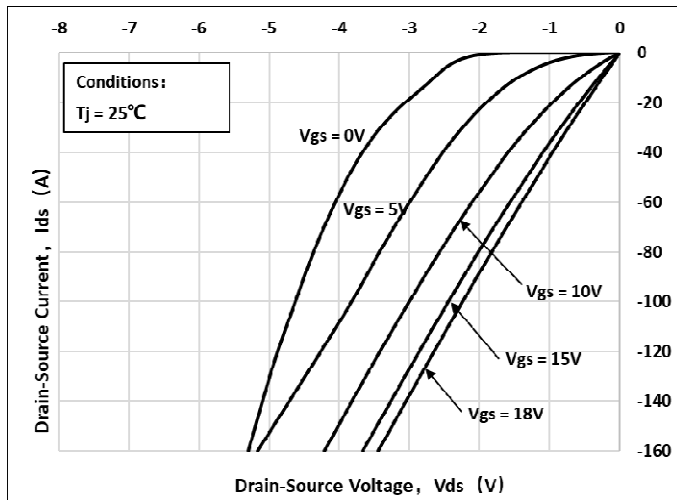


Fig 14: 3rd Quadrant Characteristic($T_J=175^\circ\text{C}$)

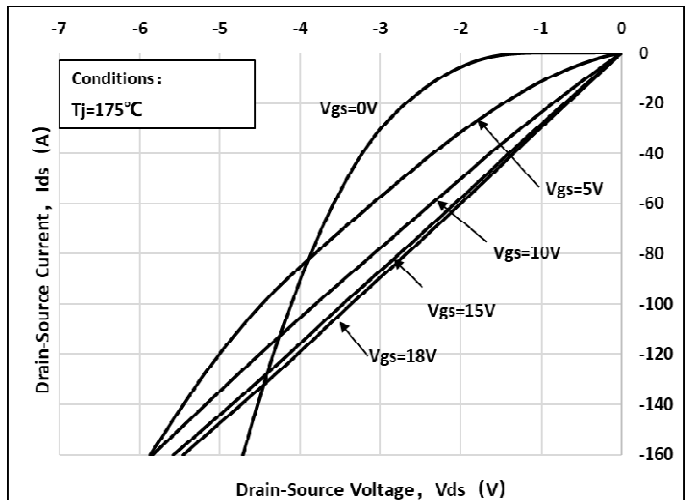


Fig 15: Capacitance Characteristic

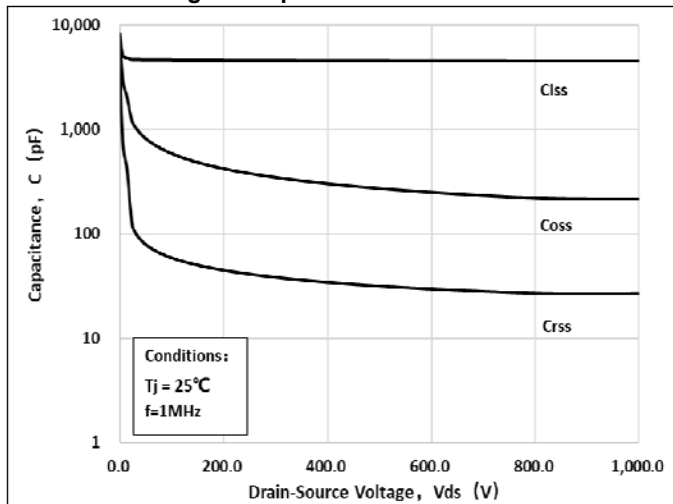


Fig 16: Safe Operating Area

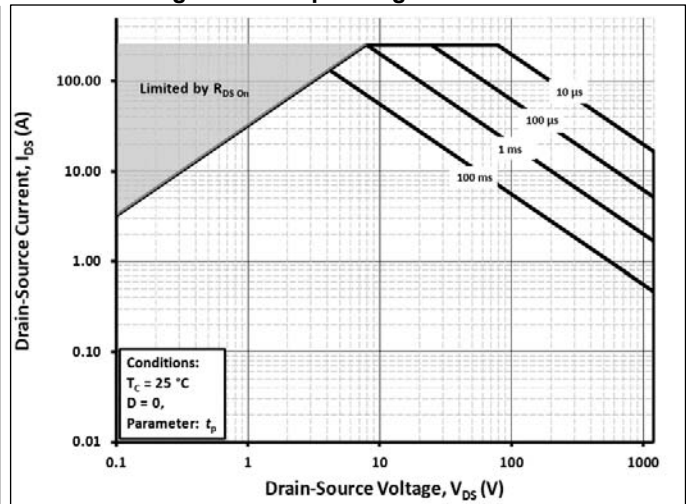
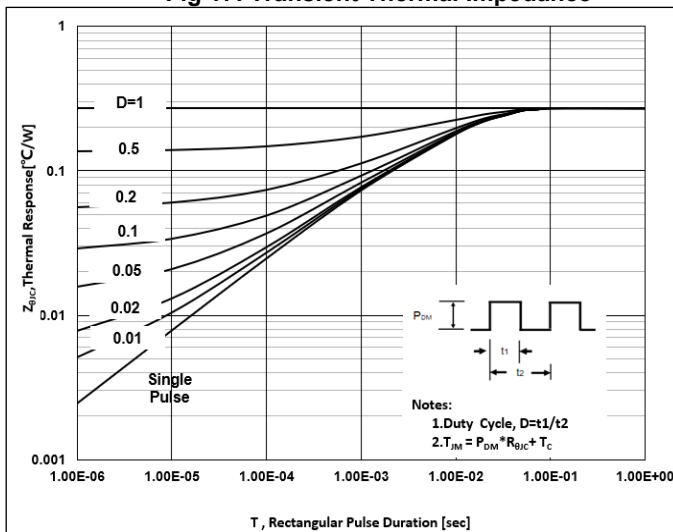


Fig 17: Transient Thermal Impedance



Test Circuit & Waveform

Figure A. Definition of switching times

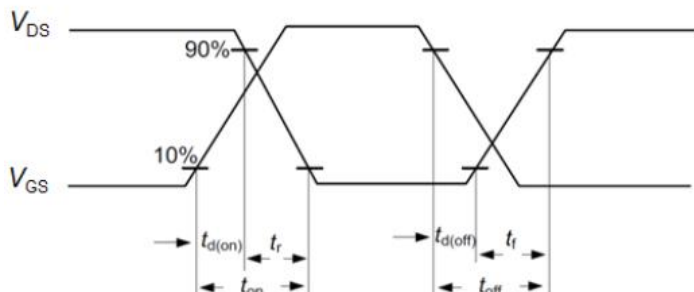


Figure B. Dynamic test circuit

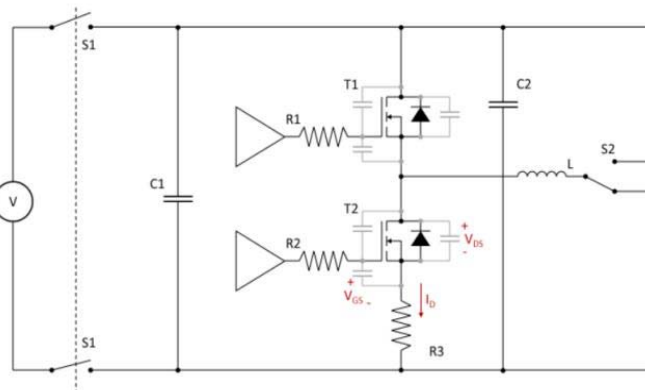


Figure C. Definition of body diodeswitching characteristics

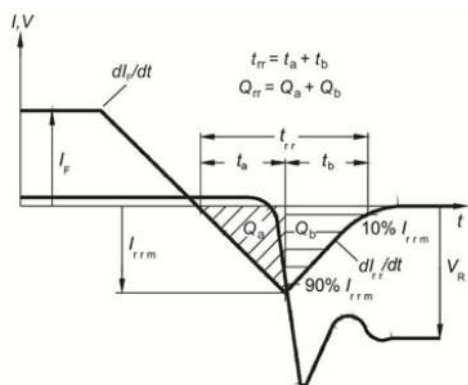
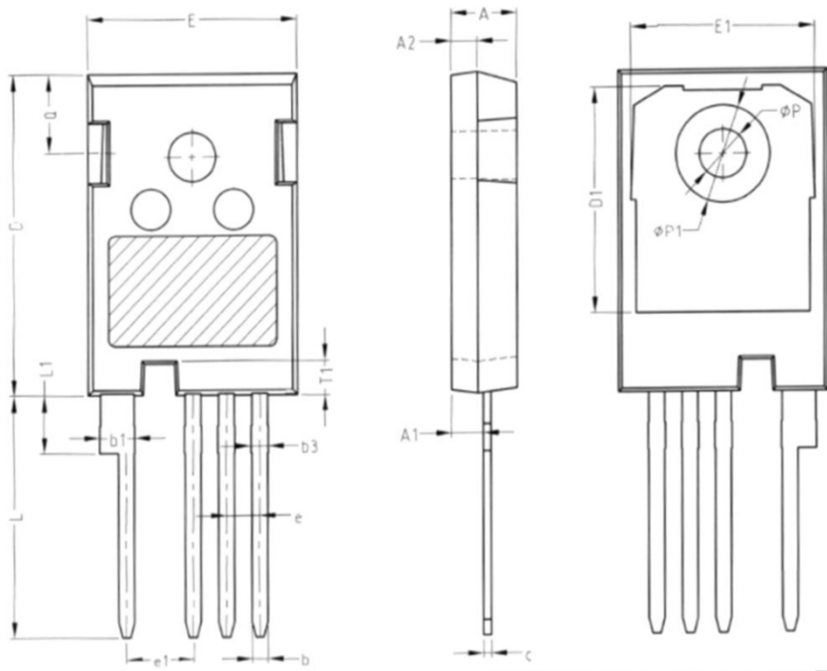


Figure C. Definition of diode switching characteristics

Package Outline:



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.80	2.00	2.20
b	1.06	1.21	1.36
b1	2.33	2.63	2.93
b3	1.07	1.30	1.60
c	0.51	0.61	0.75
D	23.30	23.45	23.60
D1	16.25	16.55	16.85
E	15.74	15.94	16.14
E1	13.72	14.02	14.32
T1	2.35	2.50	2.65
e	2.54 BSC		
e1	5.08 BSC		
Q	5.49	5.79	6.09
L	17.27	17.57	17.87
L1	3.99	4.19	4.39
ΦP	3.40	3.60	3.80
Φp1	7.19 REF		